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### Understanding [Embedded - Microprocessors](#)

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

### Applications of [Embedded - Microprocessors](#)

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

#### Details

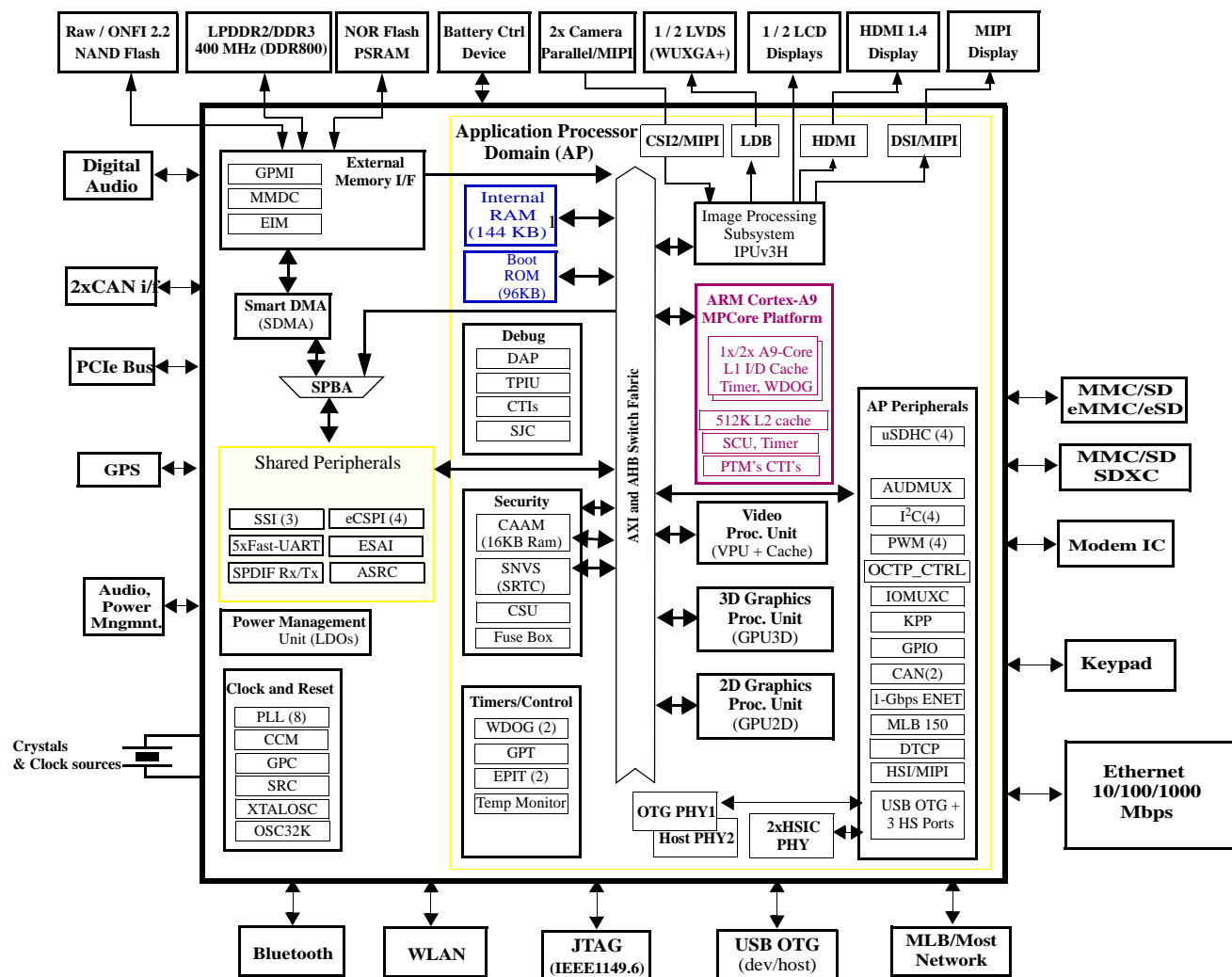
Product Status	Active
Core Processor	ARM® Cortex® -A9
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	800MHz
Co-Processors/DSP	Multimedia; NEON™ SIMD
RAM Controllers	LPDDR2, LVDDR3, DDR3
Graphics Acceleration	Yes
Display & Interface Controllers	Keypad, LCD
Ethernet	10/100/1000Mbps (1)
SATA	-
USB	USB 2.0 + PHY (4)
Voltage - I/O	1.8V, 2.5V, 2.8V, 3.3V
Operating Temperature	-40°C ~ 125°C (TJ)
Security Features	ARM TZ, Boot Security, Cryptography, RTIC, Secure Fusebox, Secure JTAG, Secure Memory, Secure RTC, Tamper Detection
Package / Case	624-LFBGA
Supplier Device Package	624-MAPBGA (21x21)
Purchase URL	<a href="https://www.e-xfl.com/product-detail/nxp-semiconductors/mcimx6s4avm08adr">https://www.e-xfl.com/product-detail/nxp-semiconductors/mcimx6s4avm08adr</a>

## 2 Architectural Overview

The following subsections provide an architectural overview of the i.MX 6Solo/6DualLite processor system.

### 2.1 Block Diagram

Figure 3 shows the functional modules in the i.MX 6Solo/6DualLite processor system.



<sup>1</sup> 144 KB RAM including 16 KB RAM inside the CAAM.

<sup>2</sup> For i.MX 6Solo, there is only one A9-core platform in the chip; for i.MX 6DualLite, there are two A9-core platforms.

**Figure 3. i.MX 6Solo/6DualLite System Block Diagram**

#### NOTE

The numbers in brackets indicate number of module instances. For example, PWM (4) indicates four separate PWM peripherals.

Table 2. i.MX 6Solo/6DualLite Modules List (continued)

Block Mnemonic	Block Name	Subsystem	Brief Description
CSU	Central Security Unit	Security	The Central Security Unit (CSU) is responsible for setting comprehensive security policy within the i.MX 6Solo/6DualLite platform.
CTI-0 CTI-1 CTI-2 CTI-3 CTI-4	Cross Trigger Interfaces	Debug / Trace	Cross Trigger Interfaces allows cross-triggering based on inputs from masters attached to CTIs. The CTI module is internal to the Cortex-A9 Core Platform.
CTM	Cross Trigger Matrix	Debug / Trace	Cross Trigger Matrix IP is used to route triggering events between CTIs. The CTM module is internal to the Cortex-A9 Core Platform.
DAP	Debug Access Port	System Control Peripherals	The DAP provides real-time access for the debugger without halting the core to: <ul style="list-style-type: none"> <li>• System memory and peripheral registers</li> <li>• All debug configuration registers</li> </ul> The DAP also provides debugger access to JTAG scan chains. The DAP module is internal to the Cortex-A9 Core Platform.
DCIC-0 DCIC-1	Display Content Integrity Checker	Automotive IP	The DCIC provides integrity check on portion(s) of the display. Each i.MX 6Solo/6DualLite processor has two such modules.
DSI	MIPI DSI i/f	Multimedia Peripherals	The MIPI DSI IP provides DSI standard display port interface. The DSI interface support 80 Mbps to 1 Gbps speed per data lane.
DTCP	DTCP	Multimedia Peripherals	Provides encryption function according to Digital Transmission Content Protection standard for traffic over MLB150.
eCSPI1-4	Configurable SPI	Connectivity Peripherals	Full-duplex enhanced Synchronous Serial Interface. It is configurable to support Master/Slave modes, four chip selects to support multiple peripherals.
ENET	Ethernet Controller	Connectivity Peripherals	<p>The Ethernet Media Access Controller (MAC) is designed to support 10/100/1000 Mbps Ethernet/IEEE 802.3 networks. An external transceiver interface and transceiver function are required to complete the interface to the media. The module has dedicated hardware to support the IEEE 1588 standard. See the ENET chapter of the reference manual for details.</p> <p><b>Note:</b> The theoretical maximum performance of 1 Gbps ENET is limited to 470 Mbps (total for Tx and Rx) due to internal bus throughput limitations. The actual measured performance in optimized environment is up to 400 Mbps. For details, see the ERR004512 erratum in the i.MX 6Solo/6DualLite errata document (IMX6SDLCE).</p>

Table 2. i.MX 6Solo/6DualLite Modules List (continued)

Block Mnemonic	Block Name	Subsystem	Brief Description
EPIT-1 EPIT-2	Enhanced Periodic Interrupt Timer	Timer Peripherals	Each EPIT is a 32-bit “set and forget” timer that starts counting after the EPIT is enabled by software. It is capable of providing precise interrupts at regular intervals with minimal processor intervention. It has a 12-bit prescaler for division of input clock frequency to get the required time setting for the interrupts to occur, and counter value can be programmed on the fly.
ESAI	Enhanced Serial Audio Interface	Connectivity Peripherals	The Enhanced Serial Audio Interface (ESAI) provides a full-duplex serial port for serial communication with a variety of serial devices, including industry-standard codecs, SPDIF transceivers, and other processors. The ESAI consists of independent transmitter and receiver sections, each section with its own clock generator. All serial transfers are synchronized to a clock. Additional synchronization signals are used to delineate the word frames. The normal mode of operation is used to transfer data at a periodic rate, one word per period. The network mode is also intended for periodic transfers; however, it supports up to 32 words (time slots) per period. This mode can be used to build time division multiplexed (TDM) networks. In contrast, the on-demand mode is intended for non-periodic transfers of data and to transfer data serially at high speed when the data becomes available. The ESAI has 12 pins for data and clocking connection to external devices.
FlexCAN-1 FlexCAN-2	Flexible Controller Area Network	Connectivity Peripherals	The CAN protocol was primarily, but not only, designed to be used as a vehicle serial data bus, meeting the specific requirements of this field: real-time processing, reliable operation in the Electromagnetic interference (EMI) environment of a vehicle, cost-effectiveness and required bandwidth. The FlexCAN module is a full implementation of the CAN protocol specification, Version 2.0 B, which supports both standard and extended message frames.
512x8 Fuse Box	Electrical Fuse Array	Security	Electrical Fuse Array. Enables to setup Boot Modes, Security Levels, Security Keys, and many other system parameters. The i.MX 6Solo/6DualLite processors consist of 512x8-bit fuse box accessible through OCOTP_CTRL interface.
GPIO-1 GPIO-2 GPIO-3 GPIO-4 GPIO-5 GPIO-6 GPIO-7	General Purpose I/O Modules	System Control Peripherals	Used for general purpose input/output to external ICs. Each GPIO module supports 32 bits of I/O.

Table 2. i.MX 6Solo/6DualLite Modules List (continued)

Block Mnemonic	Block Name	Subsystem	Brief Description
WDOG-1	Watch Dog	Timer Peripherals	The Watch Dog Timer supports two comparison points during each counting period. Each of the comparison points is configurable to evoke an interrupt to the ARM core, and a second point evokes an external event on the WDOG line.
WDOG-2 (TZ)	Watch Dog (TrustZone)	Timer Peripherals	The TrustZone Watchdog (TZ WDOG) timer module protects against TrustZone starvation by providing a method of escaping normal mode and forcing a switch to the TZ mode. TZ starvation is a situation where the normal OS prevents switching to the TZ mode. Such situation is undesirable as it can compromise the system's security. Once the TZ WDOG module is activated, it must be serviced by TZ software on a periodic basis. If servicing does not take place, the timer times out. Upon a time-out, the TZ WDOG asserts a TZ mapped interrupt that forces switching to the TZ mode. If it is still not served, the TZ WDOG asserts a security violation signal to the CSU. The TZ WDOG module cannot be programmed or deactivated by a normal mode SW.
WEIM	NOR-Flash /PSRAM interface	Connectivity Peripherals	The WEIM NOR-FLASH / PSRAM provides: <ul style="list-style-type: none"> <li>• Support 16-bit (in muxed IO mode only) PSRAM memories (sync and async operating modes), at slow frequency</li> <li>• Support 16-bit (in muxed IO mode only) NOR-Flash memories, at slow frequency</li> <li>• Multiple chip selects</li> </ul>
XTALOSC	Crystal Oscillator I/F	Clocks, Resets, and Power Control	The XTALOSC module enables connectivity to external crystal oscillator device. In a typical application use-case, it is used for 24 MHz oscillator to provide USB required frequency.

Table 10. Maximum Supply Currents (continued)

Power Line	Conditions	Max Current	Unit
NVCC_LVDS2P5 <sup>6</sup>	—	NVCC_LVDS2P5 is connected to VDD_HIGH_CAP at the board level. VDD_HIGH_CAP is capable of handling the current required by NVCC_LVDS2P5.	—
MISC			
DDR_VREF	—	1	mA

<sup>1</sup> The actual maximum current drawn from VDD\_HIGH\_IN will be as shown plus any additional current drawn from the VDD\_HIGH\_CAP outputs, depending upon actual application configuration (for example, NVCC\_LVDS2P5, NVCC\_MIP1, or HDMI and PCIe VPH supplies).

<sup>2</sup> Under normal operating conditions, the maximum current on VDD\_SNVS\_IN is shown in Table 10. The maximum VDD\_SNVS\_IN current may be higher depending on specific operating configurations, such as BOOT\_MODE[1:0] not equal to 00, or use of the Tamper feature. During initial power on, VDD\_SNVS\_IN can draw up to 1 mA if the supply is capable of sourcing that current. If less than 1 mA is available, the VDD\_SNVS\_CAP charge time will increase.

<sup>3</sup> This is the maximum current per active USB physical interface.

<sup>4</sup> The DRAM power consumption is dependent on several factors, such as external signal termination. DRAM power calculators are typically available from the memory vendors. They take in account factors, such as signal termination. See the i.MX 6Solo/DualLite Power Consumption Measurement Application Note (AN4576) for examples of DRAM power consumption during specific use case scenarios.

<sup>5</sup> General equation for estimated, maximum power consumption of an IO power supply:

$$I_{max} = N \times C \times V \times (0.5 \times F)$$

Where:

N—Number of IO pins supplied by the power line

C—Equivalent external capacitive load

V—IO voltage

(0.5 x F)—Data change rate. Up to 0.5 of the clock rate (F)

In this equation, I<sub>max</sub> is in Amps, C in Farads, V in Volts, and F in Hertz.

<sup>6</sup> NVCC\_LVDS2P5 is supplied by VDD\_HIGH\_CAP (by external connection) so the maximum supply current is included in the current shown for VDD\_HIGH\_IN. The maximum supply current for NVCC\_LVDS2P5 has not been characterized separately.

## 4.1.6 Low Power Mode Supply Currents

Table 11 shows the current core consumption (not including I/O) of i.MX 6Solo/6DualLite processors in selected low power modes.

Table 11. Stop Mode Current and Power Consumption

Mode	Test Conditions	Supply	Typical <sup>1</sup>	Units
WAIT	<ul style="list-style-type: none"> <li>ARM, SoC, and PU LDOs are set to 1.225</li> <li>HIGH LDO set to 2.5 V</li> <li>Clocks are gated.</li> <li>DDR is in self refresh.</li> <li>PLLs are active in bypass (24MHz)</li> <li>Supply Voltages remain ON</li> </ul>	VDD_ARM_IN (1.4V)	4.5	mA
		VDD_SOC_IN (1.4V)	23	
		VDD_HIGH_IN (3.0V)	13.5	
		Total	79	mW

**Table 13. PCIe PHY Current Drain (continued)**

Mode	Test Conditions	Supply	Max Current	Unit
Power Down	—	PCIE_VP (1.1 V)	1.3	mA
		PCIE_VPTX (1.1 V)	0.18	
		PCIE_VPH (2.5 V)	0.36	

### 4.1.9 HDMI Power Consumption

Table 14 provides HDMI PHY currents for both Active 3D Tx with LFSR15 data and power-down modes.

**Table 14. HDMI PHY Current Drain**

Mode	Test Conditions	Supply	Max Current	Unit
Active	Bit rate 251.75 Mbps	HDMI_VPH	14	mA
		HDMI_VP	4.1	mA
	Bit rate 279.27 Mbps	HDMI_VPH	14	mA
		HDMI_VP	4.2	mA
	Bit rate 742.5 Mbps	HDMI_VPH	17	mA
		HDMI_VP	7.5	mA
	Bit rate 1.485 Gbps	HDMI_VPH	17	mA
		HDMI_VP	12	mA
	Bit rate 2.275 Gbps	HDMI_VPH	16	mA
		HDMI_VP	17	mA
	Bit rate 2.97 Gbps	HDMI_VPH	19	mA
		HDMI_VP	22	mA
Power-down	—	HDMI_VPH	49	μA
		HDMI_VP	1100	μA

## 4.2 Power Supplies Requirements and Restrictions

The system design must comply with power-up sequence, power-down sequence, and steady state guidelines as described in this section to guarantee the reliable operation of the device. Any deviation from these sequences may result in the following situations:

- Excessive current during power-up phase
- Prevention of the device from booting
- Irreversible damage to the processor (worst-case scenario)

### 4.3.2.2 LDO\_2P5

The LDO\_2P5 module implements a programmable linear-regulator function from VDD\_HIGH\_IN (see [Table 8](#) for minimum and maximum input requirements). Typical Programming Operating Range is 2.25 V to 2.75 V with the nominal default setting as 2.5 V. LDO\_2P5 supplies the USB Phy, LVDS Phy, HDMI Phy, MIPI Phy, E-fuse module, and PLLs. A programmable brown-out detector is included in the regulator that can be used by the system to determine when the load capability of the regulator is being exceeded, to take the necessary steps. Current-limiting can be enabled to allow for in-rush current requirements during start-up, if needed. Active-pull-down can also be enabled for systems requiring this feature. An alternate self-biased low-precision weak-regulator is included that can be enabled for applications needing to keep the output voltage alive during low-power modes where the main regulator driver and its associated global bandgap reference module are disabled. The output of the weak-regulator is not programmable and is a function of the input supply as well as the load current. Typically, with a 3 V input supply the weak-regulator output is 2.525 V and its output impedance is approximately 40  $\Omega$ .

For information on external capacitor requirements for this regulator, see the Hardware Development Guide for i.MX 6Quad, 6Dual, 6DualLite, 6Solo Families of Applications Processors (IMX6DQ6SDLHDG).

For additional information, see the i.MX 6Solo/6DualLite reference manual.

### 4.3.2.3 LDO\_USB

The LDO\_USB module implements a programmable linear-regulator function from the USB\_OTG\_VBUS and USB\_H1\_VBUS voltages (4.4 V–5.25 V) to produce a nominal 3.0 V output voltage. A programmable brown-out detector is included in the regulator that can be used by the system to determine when the load capability of the regulator is being exceeded, to take the necessary steps. This regulator has a built in power-mux that allows the user to select to run the regulator from either USB\_VBUS supply, when both are present. If only one of the USB\_VBUS voltages is present, then, the regulator automatically selects this supply. Current limit is also included to help the system meet in-rush current targets.

For information on external capacitor requirements for this regulator, see the Hardware Development Guide for i.MX 6Quad, 6Dual, 6DualLite, 6Solo Families of Applications Processors (IMX6DQ6SDLHDG).

For additional information, see the i.MX 6Solo/6DualLite reference manual.



Table 24. LPDDR2 I/O DC Electrical Parameters<sup>1</sup> (continued)

Parameters	Symbol	Test Conditions	Min	Max	Unit
Input Reference Voltage	Vref	—	$0.49 \times \text{OVDD}$	$0.51 \times \text{OVDD}$	V
DC High-Level input voltage	Vih_DC	—	Vref+0.13	OVDD	V
DC Low-Level input voltage	Vil_DC	—	OVSS	Vref-0.13	V
Differential Input Logic High	Vih_diff	—	0.26	Note <sup>2</sup>	
Differential Input Logic Low	Vil_diff	—	Note <sup>3</sup>	-0.26	
Pull-up/Pull-down Impedance Mismatch	Mmpupd	—	-15	15	%
240 $\Omega$ unit calibration resolution	Rres	—	—	10	$\Omega$
Keeper Circuit Resistance	Rkeep	—	110	175	k $\Omega$
Input current (no pull-up/down)	Iin	VI = 0, VI = OVDD	-2.5	2.5	$\mu\text{A}$

<sup>1</sup> Note that the JEDEC LPDDR2 specification (JESD209\_2B) supersedes any specification in this document.

<sup>2</sup> The single-ended signals need to be within the respective limits (Vih(dc) max, Vil(dc) min) for single-ended signals as well as the limitations for overshoot and undershoot.

<sup>3</sup> The single-ended signals need to be within the respective limits (Vih(dc) max, Vil(dc) min) for single-ended signals as well as the limitations for overshoot and undershoot.

#### 4.6.3.2 DDR3/DDR3L Mode I/O DC Parameters

The parameters in Table 25 are guaranteed per the operating ranges in Table 8, unless otherwise noted. For details on supported DDR memory configurations, see Section 4.9.4, “Multi-Mode DDR Controller (MMDC).”

Table 25. DDR3/DDR3L I/O DC Electrical Characteristics<sup>1</sup>

Parameters	Symbol	Test Conditions	Min	Max	Unit
High-level output voltage	VOH	Ioh= -0.1mA Voh (for DSE=001)	$0.8 \times \text{OVDD}^2$	—	V
Low-level output voltage	VOL	Iol= 0.1mA Vol (for DSE=001)	—	$0.2 \times \text{OVDD}$	V
High-level output voltage	VOH	Ioh= -1mA Voh (for all except DSE=001)	$0.8 \times \text{OVDD}$	—	V
Low-level output voltage	VOL	Iol= 1mA Vol (for all except DSE=001)	—	$0.2 \times \text{OVDD}$	V
Input Reference Voltage	Vref	—	$0.49 \times \text{OVDD}$	$0.51 \times \text{OVDD}$	V
DC High-Level input voltage	Vih_DC	—	Vref <sup>3</sup> +0.1	OVDD	V
DC Low-Level input voltage	Vil_DC	—	OVSS	Vref-0.1	V
Differential Input Logic High	Vih_diff	—	0.2	See Note <sup>4</sup>	V
Differential Input Logic Low	Vil_diff	—	See Note <sup>3</sup>	-0.2	V
Termination Voltage	Vtt	Vtt tracking OVDD/2	$0.49 \times \text{OVDD}$	$0.51 \times \text{OVDD}$	V
Pull-up/Pull-down Impedance Mismatch	Mmpupd	—	-10	10	%

Table 28. MLB I/O DC Characteristics

Parameter	Symbol	Test Conditions	Min	Max	Unit
Output Differential Voltage	VOD	Rload-50Ω Diff	300	500	mV
Output High Voltage	VOH	Rload-50Ω Diff	1.25	1.75	V
Output Low Voltage	VOL	Rload-50Ω Diff	0.75	1.25	V
Common-mode output voltage ((Vpadp*+Vpadn*)/2)	Vocm	Rload-50Ω Diff	1	1.5	V
Differential output impedance	Zo	—	1.6	—	kΩ

## 4.7 I/O AC Parameters

This section includes the AC parameters of the following I/O types:

- General Purpose I/O (GPIO)
- Double Data Rate I/O (DDR) for LPDDR2 and DDR3/DDR3L modes
- LVDS I/O
- MLB I/O

The GPIO and DDR I/O load circuit and output transition time waveforms are shown in [Figure 5](#) and [Figure 6](#).

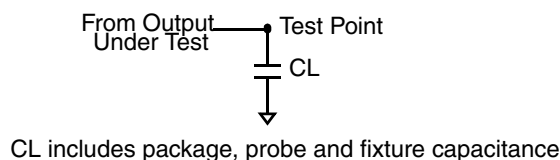


Figure 5. Load Circuit for Output

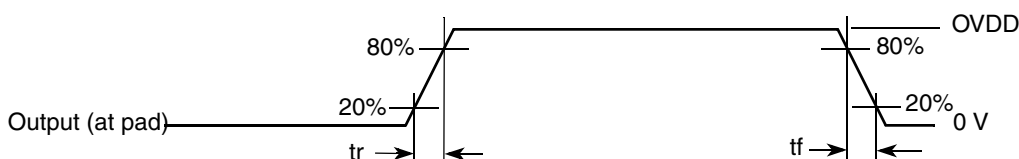


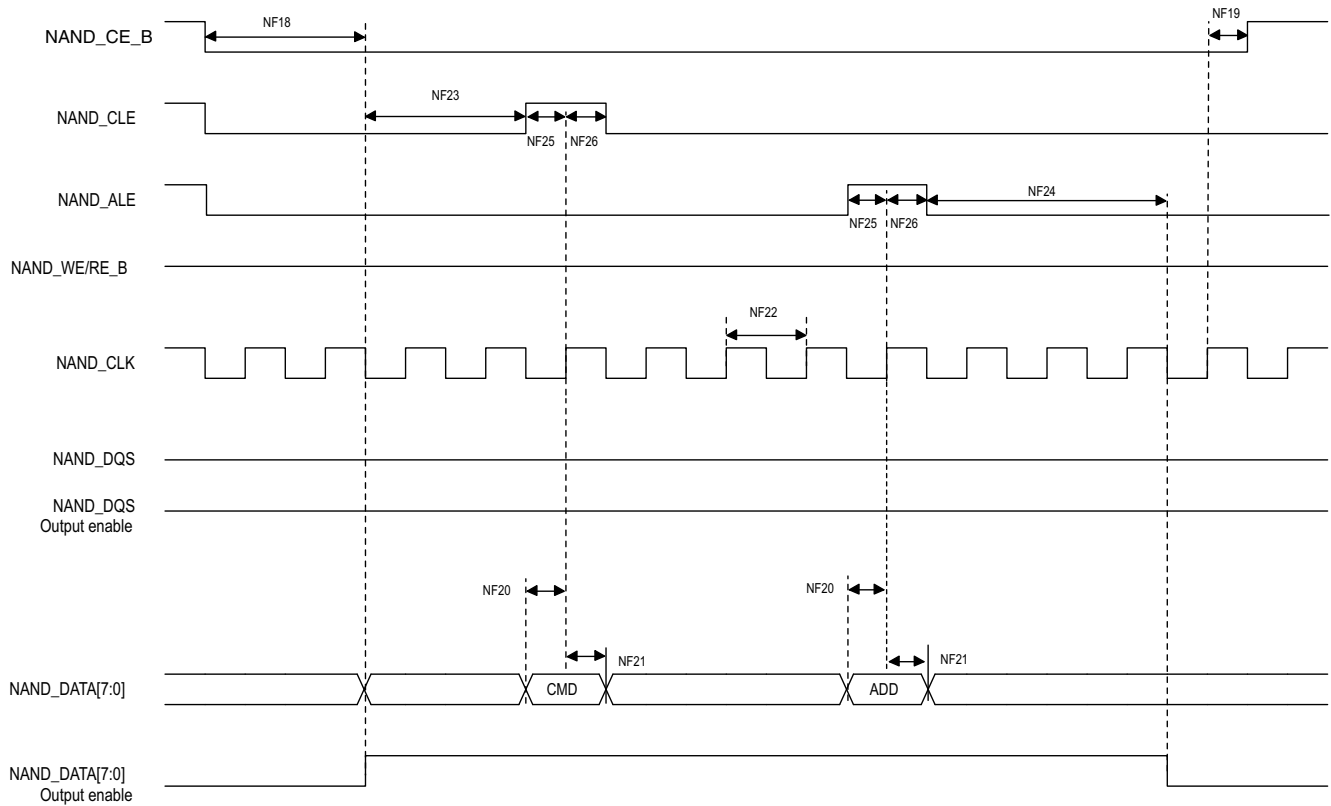
Figure 6. Output Transition Time Waveform

### 4.7.1 General Purpose I/O AC Parameters

The I/O AC parameters for GPIO in slow and fast modes are presented in the [Table 29](#) and [Table 30](#), respectively. Note that the fast or slow I/O behavior is determined by the appropriate control bits in the IOMUXC control registers.

## 4.10.2 Source Synchronous Mode AC Timing (ONFI 2.x Compatible)

Figure 30 to Figure 32 show the write and read timing of Source Synchronous Mode.



**Figure 30. Source Synchronous Mode Command and Address Timing Diagram**

Table 48. Samsung Toggle Mode Timing Parameters<sup>1</sup> (continued)

ID	Parameter	Symbol	Timing T = GPMI Clock Cycle		Unit
			Min	Max	
NF28	Data write setup	tDS <sup>6</sup>	$0.25 \times tCK - 0.32$	—	ns
NF29	Data write hold	tDH <sup>6</sup>	$0.25 \times tCK - 0.79$	—	ns
NF30	NAND_DQS/NAND_DQ read setup skew	tDQSQ <sup>7</sup>	—	3.18	
NF31	NAND_DQS/NAND_DQ read hold skew	tQHS <sup>7</sup>	—	3.27	

<sup>1</sup> The GPMI toggle mode output timing can be controlled by the module's internal registers HW\_GPMI\_TIMING0\_ADDRESS\_SETUP, HW\_GPMI\_TIMING0\_DATA\_SETUP, and HW\_GPMI\_TIMING0\_DATA\_HOLD. This AC timing depends on these registers settings. In the table, AS/DS/DH represents each of these settings.

<sup>2</sup> AS minimum value can be 0, while DS/DH minimum value is 1.

<sup>3</sup> T = tCK (GPMI clock period) - 0.075ns (half of maximum p-p jitter).

<sup>4</sup> CE\_DELAY represents HW\_GPMI\_TIMING2[CE\_DELAY]. NF18 is guaranteed by the design. Read/Write operation is started with enough time of ALE/CLE assertion to low level.

<sup>5</sup> PRE\_DELAY+1) ≥ (AS+DS).

<sup>6</sup> Shown in Figure 34, Samsung Toggle Mode Data Write Timing diagram.

<sup>7</sup> Shown in Figure 33, NAND\_DQS/NAND\_DQ Read Valid Window.

For DDR Toggle mode, Figure 33 shows the timing diagram of NAND\_DQS/NAND\_DATAxx read valid window. The typical value of tDQSQ is 1.4 ns (max) and 1.4 ns (max) for tQHS at 133 MB/s. GPMI will sample NAND\_DATA[7:0] at both rising and falling edge of a delayed NAND\_DQS signal, which is provided by an internal DPLL. The delay value of this register can be controlled by GPMI register GPMI\_READ\_DDR\_DLL\_CTRL.SLV\_DLY\_TARGET (see the GPMI chapter of the i.MX 6Solo/6DualLite reference manual). Generally, the typical delay value is equal to 0x7 which means 1/4 clock cycle delay expected. But if the board delay is big enough and cannot be ignored, the delay value should be made larger to compensate the board delay.

## 4.11 External Peripheral Interface Parameters

The following subsections provide information on external peripheral interfaces.

### 4.11.1 AUDMUX Timing Parameters

The AUDMUX provides a programmable interconnect logic for voice, audio, and data routing between internal serial interfaces (SSIs) and external serial interfaces (audio and voice codecs). The AC timing of AUDMUX external pins is governed by the SSI module. For more information, see the respective SSI electrical specifications found within this document.

### 4.11.2 ECSPI Timing Parameters

This section describes the timing parameters of the ECSPI blocks. The ECSPI have separate timing parameters for master and slave modes.

Table 51. Enhanced Serial Audio Interface (ESAI) Timing Parameters (continued)

No.	Characteristics <sup>1,2</sup>	Symbol	Expression <sup>2</sup>	Min	Max	Condition <sup>3</sup>	Unit
81	ESAI_TX_CLK rising edge to ESAI_TX_FS out (wr) low <sup>5</sup>	— —	— —	— —	22.0 12.0	x ck i ck	ns
82	ESAI_TX_CLK rising edge to ESAI_TX_FS out (wl) high	— —	— —	— —	19.0 9.0	x ck i ck	ns
83	ESAI_TX_CLK rising edge to ESAI_TX_FS out (wl) low	— —	— —	— —	20.0 10.0	x ck i ck	ns
84	ESAI_TX_CLK rising edge to data out enable from high impedance	— —	— —	— —	22.0 17.0	x ck i ck	ns
86	ESAI_TX_CLK rising edge to data out valid	— —	— —	— —	18.0 13.0	x ck i ck	ns
87	ESAI_TX_CLK rising edge to data out high impedance <sup>67</sup>	— —	— —	— —	21.0 16.0	x ck i ck	ns
89	ESAI_TX_FS input (bl, wr) setup time before ESAI_TX_CLK falling edge <sup>5</sup>	— —	— —	2.0 18.0	— —	x ck i ck	ns
90	ESAI_TX_FS input (wl) setup time before ESAI_TX_CLK falling edge	— —	— —	2.0 18.0	— —	x ck i ck	ns
91	ESAI_TX_FS input hold time after ESAI_TX_CLK falling edge	— —	— —	4.0 5.0	— —	x ck i ck	ns
95	ESAI_RX_HF_CLK/ESAI_TX_HF_CLK clock cycle	—	$2 \times T_C$	15	—	—	ns
96	ESAI_TX_HF_CLK input rising edge to ESAI_TX_CLK output	—	—	—	18.0	—	ns
97	ESAI_RX_HF_CLK input rising edge to ESAI_RX_CLK output	—	—	—	18.0	—	ns

- <sup>1</sup> i ck = internal clock  
x ck = external clock  
i ck a = internal clock, asynchronous mode  
(asynchronous implies that ESAI\_TX\_CLK and ESAI\_RX\_CLK are two different clocks)  
i ck s = internal clock, synchronous mode  
(synchronous implies that ESAI\_TX\_CLK and ESAI\_RX\_CLK are the same clock)

- <sup>2</sup> bl = bit length  
wl = word length  
wr = word length relative

- <sup>3</sup> ESAI\_TX\_CLK(SCKT pin) = transmit clock  
ESAI\_RX\_CLK(SCKR pin) = receive clock  
ESAI\_TX\_FS(FST pin) = transmit frame sync  
ESAI\_RX\_FS(FSR pin) = receive frame sync  
ESAI\_TX\_HF\_CLK(HCKT pin) = transmit high frequency clock  
ESAI\_RX\_HF\_CLK(HCKR pin) = receive high frequency clock

- <sup>4</sup> For the internal clock, the external clock cycle is defined by  $I_{cyc}$  and the ESAI control register.

- <sup>5</sup> The word-relative frame sync signal waveform relative to the clock operates in the same manner as the bit-length frame sync signal waveform, but it spreads from one serial clock before the first bit clock (like the bit length frame sync signal), until the second-to-last bit clock of the first word in the frame.

- <sup>6</sup> Periodically sampled and not 100% tested.

#### 4.11.4.4 Bus Operation Condition for 3.3 V and 1.8 V Signaling

Signaling level of SD/eMMC4.3 and eMMC4.4/4.41 modes is 3.3 V. Signaling level of SDR104/SDR50 mode is 1.8 V. The DC parameters for the NVCC\_SD1, NVCC\_SD2 and NVCC\_SD3 supplies are identical to those shown in [Table 23, "GPIO DC Parameters," on page 41](#).

#### 4.11.5 Ethernet Controller (ENET) AC Electrical Specifications

The following timing specs are defined at the chip I/O pin and must be translated appropriately to arrive at timing specs/constraints for the physical interface.

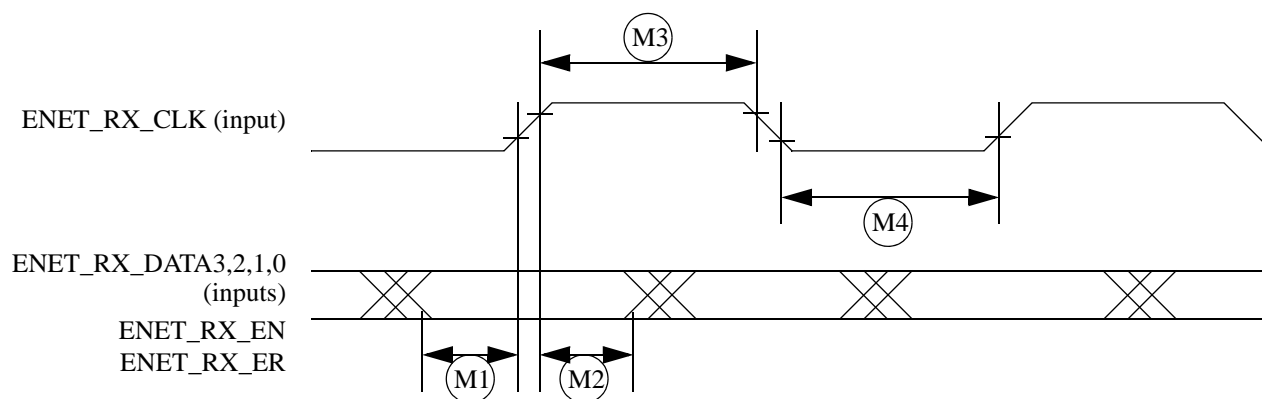
##### 4.11.5.1 ENET MII Mode Timing

This subsection describes MII receive, transmit, asynchronous inputs, and serial management signal timings.

##### 4.11.5.1.1 MII Receive Signal Timing (ENET\_RX\_DATA3,2,1,0, ENET\_RX\_EN, ENET\_RX\_ER, and ENET\_RX\_CLK)

The receiver functions correctly up to an ENET\_RX\_CLK maximum frequency of 25 MHz + 1%. There is no minimum frequency requirement. Additionally, the processor clock frequency must exceed twice the ENET\_RX\_CLK frequency.

[Figure 43](#) shows MII receive signal timings. [Table 55](#) describes the timing parameters (M1–M4) shown in the figure.



**Figure 43. MII Receive Signal Timing Diagram**

**Table 55. MII Receive Signal Timing**

ID	Characteristic <sup>1</sup>	Min	Max	Unit
M1	ENET_RX_DATA3,2,1,0, ENET_RX_EN, ENET_RX_ER to ENET_RX_CLK setup	5	—	ns
M2	ENET_RX_CLK to ENET_RX_DATA3,2,1,0, ENET_RX_EN, ENET_RX_ER hold	5	—	ns
M3	ENET_RX_CLK pulse width high	35%	65%	ENET_RX_CLK period
M4	ENET_RX_CLK pulse width low	35%	65%	ENET_RX_CLK period

<sup>1</sup> ENET\_RX\_EN, ENET\_RX\_CLK, and ENET0\_RXD0 have the same timing in 10 Mbps 7-wire interface mode.

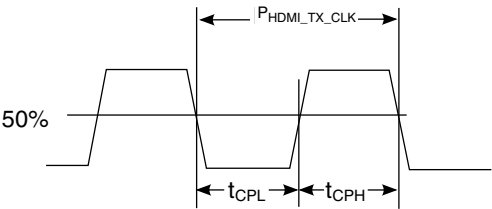


Figure 54. TMDS Clock Signal Definitions

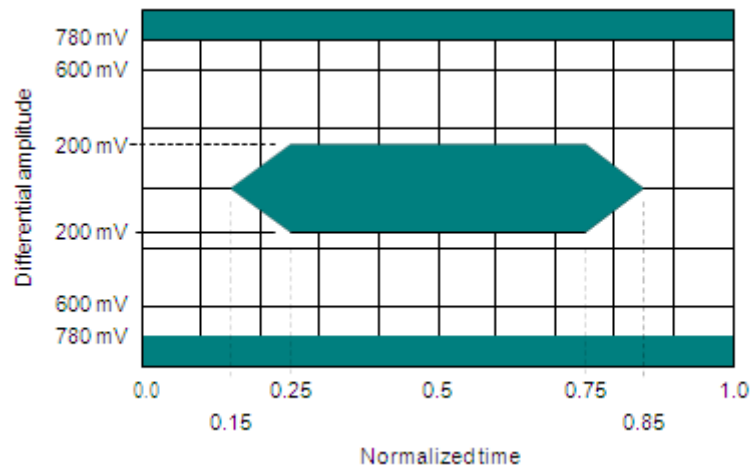


Figure 55. Eye Diagram Mask Definition for HDMI Driver Signal Specification at TP1

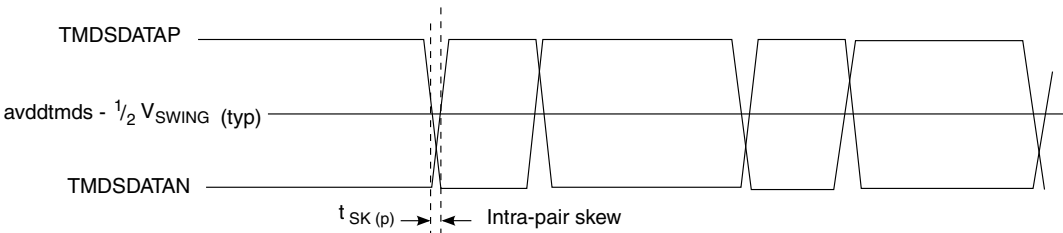


Figure 56. Intra-Pair Skew Definition

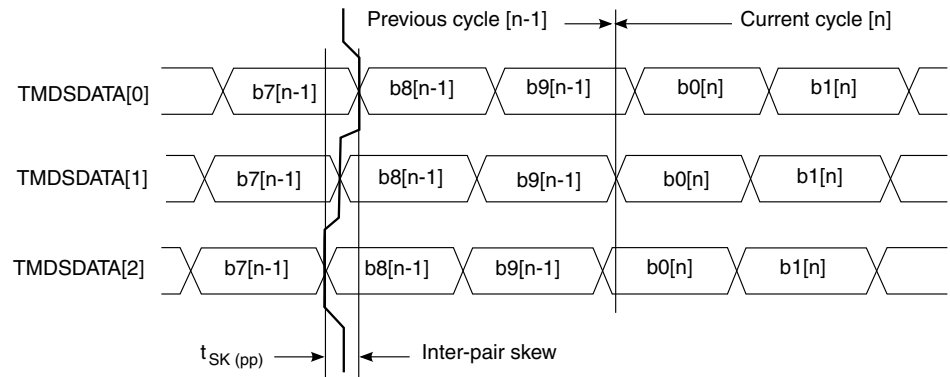


Figure 57. Inter-Pair Skew Definition

### 4.11.9 I<sup>2</sup>C Module Timing Parameters

This section describes the timing parameters of the I<sup>2</sup>C module. Figure 59 depicts the timing of I<sup>2</sup>C module, and Table 63 lists the I<sup>2</sup>C module timing characteristics.

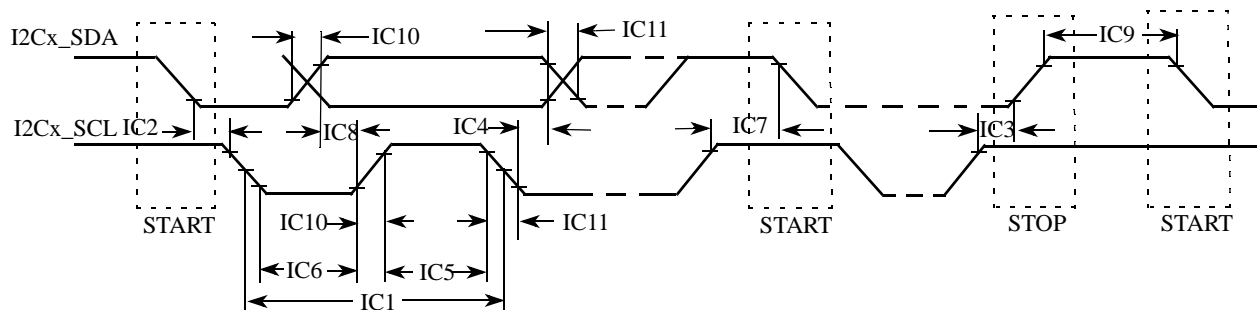


Figure 59. I<sup>2</sup>C Bus Timing

Table 63. I<sup>2</sup>C Module Timing Parameters

ID	Parameter	Standard Mode		Fast Mode		Unit
		Min	Max	Min	Max	
IC1	I2Cx_SCL cycle time	10	—	2.5	—	μs
IC2	Hold time (repeated) START condition	4.0	—	0.6	—	μs
IC3	Set-up time for STOP condition	4.0	—	0.6	—	μs
IC4	Data hold time	0 <sup>1</sup>	3.45 <sup>2</sup>	0 <sup>1</sup>	0.9 <sup>2</sup>	μs
IC5	HIGH Period of I2Cx_SCL Clock	4.0	—	0.6	—	μs
IC6	LOW Period of the I2Cx_SCL Clock	4.7	—	1.3	—	μs
IC7	Set-up time for a repeated START condition	4.7	—	0.6	—	μs
IC8	Data set-up time	250	—	100 <sup>3</sup>	—	ns
IC9	Bus free time between a STOP and START condition	4.7	—	1.3	—	μs
IC10	Rise time of both I2Cx_SDA and I2Cx_SCL signals	—	1000	$20 + 0.1C_b$ <sup>4</sup>	300	ns
IC11	Fall time of both I2Cx_SDA and I2Cx_SCL signals	—	300	$20 + 0.1C_b$ <sup>4</sup>	300	ns
IC12	Capacitive load for each bus line (C <sub>b</sub> )	—	400	—	400	pF

<sup>1</sup> A device must internally provide a hold time of at least 300 ns for I2Cx\_SDA signal to bridge the undefined region of the falling edge of I2Cx\_SCL.

<sup>2</sup> The maximum hold time has only to be met if the device does not stretch the LOW period (ID no IC5) of the I2Cx\_SCL signal.

<sup>3</sup> A Fast-mode I<sup>2</sup>C-bus device can be used in a Standard-mode I<sup>2</sup>C-bus system, but the requirement of Set-up time (ID No IC7) of 250 ns must be met. This automatically is the case if the device does not stretch the LOW period of the I2Cx\_SCL signal. If such a device does stretch the LOW period of the I2Cx\_SCL signal, it must output the next data bit to the I2Cx\_SDA line  $\text{max\_rise\_time (IC9)} + \text{data\_setup\_time (IC7)} = 1000 + 250 = 1250$  ns (according to the Standard-mode I<sup>2</sup>C-bus specification) before the I2Cx\_SCL line is released.

<sup>4</sup> C<sub>b</sub> = total capacitance of one bus line in pF.



Table 84. SSI Transmitter Timing with External Clock (continued)

ID	Parameter	Min	Max	Unit
<b>Synchronous External Clock Operation</b>				
SS44	AUDx_RXD setup before AUDx_TXC falling	10.0	—	ns
SS45	AUDx_RXD hold after AUDx_TXC falling	2.0	—	ns
SS46	AUDx_RXD rise/fall time	—	6.0	ns

**NOTE**

- All the timings for the SSI are given for a non-inverted serial clock polarity (TSCKP/RSCKP = 0) and a non-inverted frame sync (TFSI/RFSI = 0). If the polarity of the clock and/or the frame sync have been inverted, all the timing remains valid by inverting the clock signal AUDx\_TXC/AUDx\_RXC and/or the frame sync AUDx\_TXFS/AUDx\_RXFS shown in the tables and in the figures.
- All timings are on Audiomux Pads when SSI is being used for data transfer.
- The terms WL and BL refer to Word Length (WL) and Bit Length (BL).
- For internal Frame Sync operation using external clock, the frame sync timing is same as that of transmit data (for example, during AC97 mode of operation).

**4.11.19.4 SSI Receiver Timing with External Clock**

Figure 94 depicts the SSI receiver external clock timing and Table 85 lists the timing parameters for the receiver timing with the external clock.

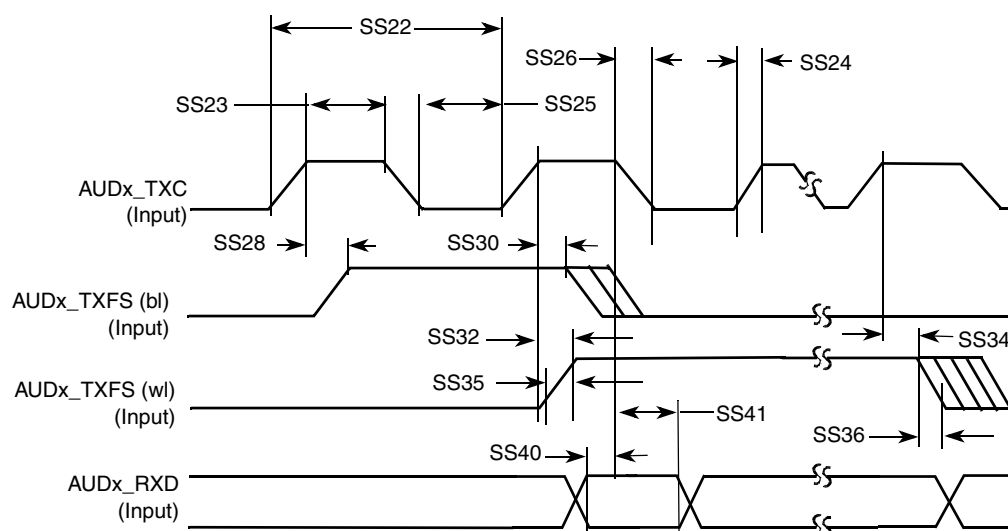
**Figure 94. SSI Receiver External Clock Timing Diagram**

Table 97. 21 x 21 mm Functional Contact Assignments (continued)

Ball Name	Ball	Power Group	Ball Type	Out of Reset Condition <sup>1</sup>			
				Default Mode (Reset Mode)	Default Function	Input/Output	Value <sup>2</sup>
DRAM_D52	AB22	NVCC_DRAM	DDR	ALT0	DRAM_DATA52	Input	100 kΩ pull-up
DRAM_D53	AC23	NVCC_DRAM	DDR	ALT0	DRAM_DATA53	Input	100 kΩ pull-up
DRAM_D54	AD25	NVCC_DRAM	DDR	ALT0	DRAM_DATA54	Input	100 kΩ pull-up
DRAM_D55	AC25	NVCC_DRAM	DDR	ALT0	DRAM_DATA55	Input	100 kΩ pull-up
DRAM_D56	AB25	NVCC_DRAM	DDR	ALT0	DRAM_DATA56	Input	100 kΩ pull-up
DRAM_D57	AA21	NVCC_DRAM	DDR	ALT0	DRAM_DATA57	Input	100 kΩ pull-up
DRAM_D58	Y25	NVCC_DRAM	DDR	ALT0	DRAM_DATA58	Input	100 kΩ pull-up
DRAM_D59	Y22	NVCC_DRAM	DDR	ALT0	DRAM_DATA59	Input	100 kΩ pull-up
DRAM_D60	AB23	NVCC_DRAM	DDR	ALT0	DRAM_DATA60	Input	100 kΩ pull-up
DRAM_D61	AA23	NVCC_DRAM	DDR	ALT0	DRAM_DATA61	Input	100 kΩ pull-up
DRAM_D62	Y23	NVCC_DRAM	DDR	ALT0	DRAM_DATA62	Input	100 kΩ pull-up
DRAM_D63	W25	NVCC_DRAM	DDR	ALT0	DRAM_DATA63	Input	100 kΩ pull-up
DRAM_D4	AC1	NVCC_DRAM	DDR	ALT0	DRAM_DATA04	Input	100 kΩ pull-up
DRAM_D5	AD1	NVCC_DRAM	DDR	ALT0	DRAM_DATA05	Input	100 kΩ pull-up
DRAM_D6	AB4	NVCC_DRAM	DDR	ALT0	DRAM_DATA06	Input	100 kΩ pull-up
DRAM_D7	AE4	NVCC_DRAM	DDR	ALT0	DRAM_DATA07	Input	100 kΩ pull-up
DRAM_D8	AD5	NVCC_DRAM	DDR	ALT0	DRAM_DATA08	Input	100 kΩ pull-up
DRAM_D9	AE5	NVCC_DRAM	DDR	ALT0	DRAM_DATA09	Input	100 kΩ pull-up
DRAM_DQM0	AC3	NVCC_DRAM	DDR	ALT0	DRAM_DQM0	Output	Low
DRAM_DQM1	AC6	NVCC_DRAM	DDR	ALT0	DRAM_DQM1	Output	Low
DRAM_DQM2	AB8	NVCC_DRAM	DDR	ALT0	DRAM_DQM2	Output	Low
DRAM_DQM3	AE10	NVCC_DRAM	DDR	ALT0	DRAM_DQM3	Output	Low
DRAM_DQM4	AB18	NVCC_DRAM	DDR	ALT0	DRAM_DQM4	Output	Low
DRAM_DQM5	AC20	NVCC_DRAM	DDR	ALT0	DRAM_DQM5	Output	Low
DRAM_DQM6	AD24	NVCC_DRAM	DDR	ALT0	DRAM_DQM6	Output	Low
DRAM_DQM7	Y21	NVCC_DRAM	DDR	ALT0	DRAM_DQM7	Output	Low
DRAM_RAS	AB15	NVCC_DRAM	DDR	ALT0	DRAM_RAS	Output	Low
DRAM_RESET	Y6	NVCC_DRAM	DDR	ALT0	DRAM_RESET	Output	Low
DRAM_SDBA0	AC15	NVCC_DRAM	DDR	ALT0	DRAM_SDBA0	Output	Low
DRAM_SDBA1	Y15	NVCC_DRAM	DDR	ALT0	DRAM_SDBA1	Output	Low
DRAM_SDBA2	AB12	NVCC_DRAM	DDR	ALT0	DRAM_SDBA2	Output	Low
DRAM_SDCKE0	Y11	NVCC_DRAM	DDR	ALT0	DRAM_SDCKE0	Output	Low
DRAM_SDCKE1	AA11	NVCC_DRAM	DDR	ALT0	DRAM_SDCKE1	Output	Low
DRAM_SDCLK_0	AD15	NVCC_DRAM	DDRCLK	ALT0	DRAM_SDCLK0_P	Output	Low
DRAM_SDCLK_0_B	AE15	NVCC_DRAM	—	—	DRAM_SDCLK0_N	—	—
DRAM_SDCLK_1	AD14	NVCC_DRAM	DDRCLK	ALT0	DRAM_SDCLK1_P	Output	Low

Table 97. 21 x 21 mm Functional Contact Assignments (continued)

Ball Name	Ball	Power Group	Ball Type	Out of Reset Condition <sup>1</sup>			
				Default Mode (Reset Mode)	Default Function	Input/Output	Value <sup>2</sup>
EIM_EB1	K23	NVCC_EIM	GPIO	ALT0	EIM_EB1	Output	High
EIM_EB2	E22	NVCC_EIM	GPIO	ALT5	GPIO2_IO30	Input	100 kΩ pull-up
EIM_EB3	F23	NVCC_EIM	GPIO	ALT5	GPIO2_IO31	Input	100 kΩ pull-up
EIM_LBA	K22	NVCC_EIM	GPIO	ALT0	EIM_LBA	Output	High
EIM_OE	J24	NVCC_EIM	GPIO	ALT0	EIM_OE	Output	High
EIM_RW	K20	NVCC_EIM	GPIO	ALT0	EIM_RW	Output	High
EIM_WAIT	M25	NVCC_EIM	GPIO	ALT0	EIM_WAIT	Input	100 kΩ pull-up
ENET_CRS_DV	U21	NVCC_ENET	GPIO	ALT5	GPIO1_IO25	Input	100 kΩ pull-up
ENET_MDC	V20	NVCC_ENET	GPIO	ALT5	GPIO1_IO31	Input	100 kΩ pull-up
ENET_MDIO	V23	NVCC_ENET	GPIO	ALT5	GPIO1_IO22	Input	100 kΩ pull-up
ENET_REF_CLK <sup>3</sup>	V22	NVCC_ENET	GPIO	ALT5	GPIO1_IO23	Input	100 kΩ pull-up
ENET_RX_ER	W23	NVCC_ENET	GPIO	ALT5	GPIO1_IO24	Input	100 kΩ pull-up
ENET_RXD0	W21	NVCC_ENET	GPIO	ALT5	GPIO1_IO27	Input	100 kΩ pull-up
ENET_RXD1	W22	NVCC_ENET	GPIO	ALT5	GPIO1_IO26	Input	100 kΩ pull-up
ENET_TX_EN	V21	NVCC_ENET	GPIO	ALT5	GPIO1_IO28	Input	100 kΩ pull-up
ENET_TXD0	U20	NVCC_ENET	GPIO	ALT5	GPIO1_IO30	Input	100 kΩ pull-up
ENET_TXD1	W20	NVCC_ENET	GPIO	ALT5	GPIO1_IO29	Input	100 kΩ pull-up
GPIO_0	T5	NVCC_GPIO	GPIO	ALT5	GPIO1_IO00	Input	100 kΩ pull-down
GPIO_1	T4	NVCC_GPIO	GPIO	ALT5	GPIO1_IO01	Input	100 kΩ pull-up
GPIO_16	R2	NVCC_GPIO	GPIO	ALT5	GPIO7_IO11	Input	100 kΩ pull-up
GPIO_17	R1	NVCC_GPIO	GPIO	ALT5	GPIO7_IO12	Input	100 kΩ pull-up
GPIO_18	P6	NVCC_GPIO	GPIO	ALT5	GPIO7_IO13	Input	100 kΩ pull-up
GPIO_19	P5	NVCC_GPIO	GPIO	ALT5	GPIO4_IO05	Input	100 kΩ pull-up
GPIO_2	T1	NVCC_GPIO	GPIO	ALT5	GPIO1_IO02	Input	100 kΩ pull-up
GPIO_3	R7	NVCC_GPIO	GPIO	ALT5	GPIO1_IO03	Input	100 kΩ pull-up
GPIO_4	R6	NVCC_GPIO	GPIO	ALT5	GPIO1_IO04	Input	100 kΩ pull-up
GPIO_5	R4	NVCC_GPIO	GPIO	ALT5	GPIO1_IO05	Input	100 kΩ pull-up
GPIO_6	T3	NVCC_GPIO	GPIO	ALT5	GPIO1_IO06	Input	100 kΩ pull-up
GPIO_7	R3	NVCC_GPIO	GPIO	ALT5	GPIO1_IO07	Input	100 kΩ pull-up
GPIO_8	R5	NVCC_GPIO	GPIO	ALT5	GPIO1_IO08	Input	100 kΩ pull-up
GPIO_9	T2	NVCC_GPIO	GPIO	ALT5	GPIO1_IO09	Input	100 kΩ pull-up
HDMI_CLKM	J5	HDMI	—	—	HDMI_TX_CLK_N	—	—
HDMI_CLKP	J6	HDMI	—	—	HDMI_TX_CLK_P	—	—
HDMI_D0M	K5	HDMI	—	—	HDMI_TX_DATA0_N	—	—
HDMI_D0P	K6	HDMI	—	—	HDMI_TX_DATA0_P	—	—
HDMI_D1M	J3	HDMI	—	—	HDMI_TX_DATA1_N	—	—

Table 100. 21 x 21 mm, 0.8 mm Pitch Ball Map i.MX 6DualLite (continued)

	AE	AD	AC	AB	AA
1	GND	DRAM_D5	DRAM_D4	LVDS1_TX2_N	LVDS1_TX1_P
2	DRAM_D1	DRAM_D0	DRAM_VREF	LVDS1_TX2_P	LVDS1_TX1_N
3	DRAM_SDQS0	DRAM_SDQS0_B	DRAM_DQM0	GND	LVDS1_TX3_N
4	DRAM_D7	GND	DRAM_D2	DRAM_D6	LVDS1_TX3_P
5	DRAM_D9	DRAM_D8	DRAM_D13	DRAM_D12	DRAM_D3
6	DRAM_SDQS1_B	DRAM_SDQS1	DRAM_DQM1	DRAM_D14	DRAM_D10
7	DRAM_D11	GND	DRAM_D15	DRAM_D16	GND
8	DRAM_SDQS2_B	DRAM_SDQS2	DRAM_D22	DRAM_DQM2	DRAM_D17
9	DRAM_D24	DRAM_D29	DRAM_D28	DRAM_D18	DRAM_D23
10	DRAM_DQM3	GND	DRAM_SDQS3	DRAM_SDQS3_B	GND
11	DRAM_D26	DRAM_D30	DRAM_D31	DRAM_D27	DRAM_SDCKE1
12	DRAM_A9	DRAM_A12	DRAM_A11	DRAM_SDBA2	DRAM_A14
13	DRAM_A5	GND	DRAM_A6	DRAM_A8	GND
14	DRAM_SDCLK_1_B	DRAM_SDCLK_1	DRAM_A0	DRAM_A1	DRAM_A2
15	DRAM_SDCLK_0_B	DRAM_SDCLK_0	DRAM_SDBA0	DRAM_RAS	DRAM_A10
16	DRAM_CAS	GND	DRAM_SDODT0	DRAM_SDWE	GND
17	ZQPAD	DRAM_CS1	DRAM_A13	DRAM_SDODT1	DRAM_D32
18	DRAM_SDQS4_B	DRAM_SDQS4	DRAM_D34	DRAM_DQM4	DRAM_D33
19	DRAM_D35	GND	DRAM_D39	DRAM_D38	GND
20	DRAM_SDQS5_B	DRAM_SDQS5	DRAM_DQM5	DRAM_D41	DRAM_D45
21	DRAM_D46	DRAM_D43	DRAM_D47	DRAM_D42	DRAM_D57
22	DRAM_D49	GND	DRAM_D48	DRAM_D52	GND
23	DRAM_SDQS6_B	DRAM_SDQS6	DRAM_D53	DRAM_D60	DRAM_D61
24	DRAM_D50	DRAM_DQM6	DRAM_D51	GND	DRAM_SDQS7_B
25	GND	DRAM_D54	DRAM_D55	DRAM_D56	DRAM_SDQS7
	AE	AD	AC	AB	AA

## 7 Revision History

[Table 101](#) provides the current revision history for this data sheet. [Table 102](#) provides a revision history for previous revisions.

**Table 101. i.MX 6Solo/6DualLite Data Sheet Document Rev. 8 History**

Rev. Number	Date	Substantive Changes
8	09/2017	<ul style="list-style-type: none"> <li>Replaced ipp_dse with DSE throughout.</li> <li><a href="#">Section 1, "Introduction"</a>: Replaced text "low voltage DDR3" with "DDR3L" in the features list of i.MX 6Solo/6DualLite applications processors.</li> <li><a href="#">Table 1, "Example Orderable Part Numbers," on page 3</a>: Added orderable part numbers.</li> <li><a href="#">Figure 1</a>: Updated to include Rev 1.4 in Silicon Revision section.</li> <li><a href="#">Section 2.1, "Block Diagram"</a>: Updated WEIM with EIM in the block diagram.</li> <li><a href="#">Table 2, "i.MX 6Solo/6DualLite Modules List," on page 11</a>: Rearranged alphabetically.</li> <li><a href="#">Table 6, "Absolute Maximum Ratings," on page 24</a>: <ul style="list-style-type: none"> <li>Removed VDD_HIGH_IN supply voltage (LDO bypass) parameter.</li> <li>Max. value of VDD_HIGH_CAP supply output voltage corrected to 2.85V.</li> </ul> </li> <li><a href="#">Table 22</a>: Updated test condition of "XTALI input leakage current at startup" parameter; replaced 32KHz RTC with 24MHz.</li> <li>Added <a href="#">Section 4.6.4, "RGMII I/O 2.5V I/O DC Electrical Parameters"</a>.</li> <li><a href="#">Section 4.8.2, "DDR I/O Output Buffer Impedance"</a>: Modified introductory text.</li> <li>Corrected <a href="#">Figure 22, "Asynchronous A/D Muxed Write Access," on page 60</a>.</li> <li><a href="#">Table 53, "eMMC4.4/4.41 Interface Timing Specification," on page 80</a>: <ul style="list-style-type: none"> <li>Added the following footnote to Card Input Clock section: 1 Clock duty cycle will be in the range of 47% to 53%.</li> <li>Min. value of uSDHC Input Setup Time reduced to 1.7ns.</li> </ul> </li> </ul>